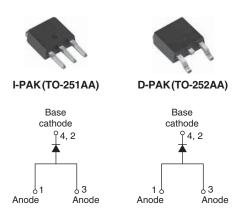


Vishay Semiconductors

# High Performance Schottky Generation 5.0, 20 A



VS-20WT04FN

PRODUCT SUMMARY					
Package	D-PAK (TO-252AA), I-PAK (TO-251AA)				
I <sub>F(AV)</sub>	20 A				
$V_{R}$	45 V				
V <sub>F</sub> at I <sub>F</sub>	0.53 V				
I <sub>RM</sub> max.	7 mA at 125 °C				
$T_J$ max.	175 °C				
Diode variation	Single die				
E <sub>AS</sub>	108 mJ				

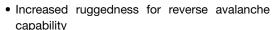
#### Note

 $\bullet~$  VF measured at 125 °C, connecting 2 anode pins

VS-20UT04

#### **FEATURES**

- 175 °C high performance Schottky diode
- · Very low forward voltage drop
- · Extremely low reverse leakage
- Optimized V<sub>F</sub> vs. I<sub>R</sub> trade off for high efficiency



- RBSOA available
- · Negligible switching losses
- Submicron trench technology
- Compliant to RoHS Directive 2002/95/EC

#### **APPLICATIONS**

- · Specific for PV cells bypass diode
- High efficiency SMPS
- High frequency switching
- Output rectification
- · Reverse battery protection
- Freewheeling
- DC/DC systems
- Increased power density systems

MAJOR RATINGS AND CHARACTERISTICS					
SYMBOL	CHARACTERISTICS	VALUES	UNITS		
V <sub>RRM</sub>		45	V		
V <sub>F</sub>	20 Apk, T <sub>J</sub> = 125 °C (typical, measured connecting 2 anode pins)	0.480	V		
T <sub>J</sub>	Range	- 55 to 175	°C		

VOLTAGE RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VS-20UT04 VS-20WT04FN	UNITS
Maximum DC reverse voltage	$V_{R}$	T <sub>J</sub> = 25 °C	45	V

# VS-20UT04, VS-20WT04FN

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ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum average forward current	I <sub>F(AV)</sub>	50 % duty cycle at T <sub>C</sub> = 153 °C, rectangular waveform		20	Α
Maximum peak one cycle	1	5 µs sine or 3 µs rect. pulse	Following any rated load condition and with rated	900	Α
non-repetitive surge current	IFSM	10 ms sine or 6 ms rect. pulse	V <sub>RRM</sub> applied <sup>(1)</sup>	220	4
Non-repetitive avalanche energy	E <sub>AS</sub>	$T_J = 25  ^{\circ}\text{C},  I_{AS} = 7  \text{A},  L = 4.4  \text{mH}$		108	mJ
Repetitive avalanche current	I <sub>AR</sub>	Limited by frequency of operation and time pulse duration so that $T_J < T_J$ max. $I_{AS}$ at $T_J$ max. as a function of time pulse		I <sub>AS</sub> at T <sub>J</sub> max.	Α

#### Note

(1) Measured connecting 2 anode pins

ELECTRICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS		TYP.	MAX.	UNITS
Forward voltage drop	V <sub>FM</sub> <sup>(1)(2)</sup>	10 A	T <sub>J</sub> = 25 °C	0.505	0.540	V
		20 A		0.570	0.610	
		10 A	- T <sub>J</sub> = 125 °C	0.415	0450	
		20 A		0.520	0.580	
Reverse leakage current	I <sub>RM</sub> <sup>(1)</sup>	T <sub>J</sub> = 25 °C	V <sub>R</sub> = Rated V <sub>R</sub>	-	100	μA
		T <sub>J</sub> = 125 °C		-	7	mA
Junction capacitance	C <sub>T</sub>	$V_R$ = 5 $V_{DC}$ (test signal range 100 kHz to 1 MHz), 25 °C		1900	-	pF
Series inductance	Ls	Measured lead to lead 5 mm from package body		-	-	nH
Maximum voltage rate of change	dV/dt	Rated V <sub>R</sub>		-	10 000	V/µs

#### Notes

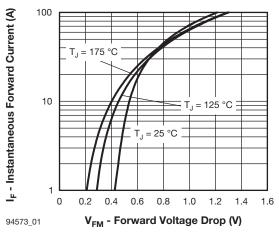
 $^{(1)}\,$  Pulse width < 300  $\mu s,$  duty cycle < 2 %

(2) Only 1 anode pin connected

THERMAL - MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		- 55 to 175	°C
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	DC operation	1.2	°C/W
Typical thermal resistance, case to heatsink	R <sub>thCS</sub>		0.3	C/VV
Approximate weight			2	g
Approximate weight			0.07	oz.
Moulding device		Case style I-PAK	20U	T04
Marking device		Case style D-PAK 20W		04FN



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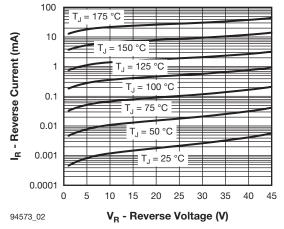


Fig. 1 - Maximum Forward Voltage Drop Characteristics

Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

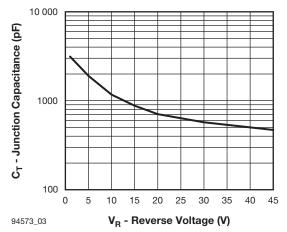


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

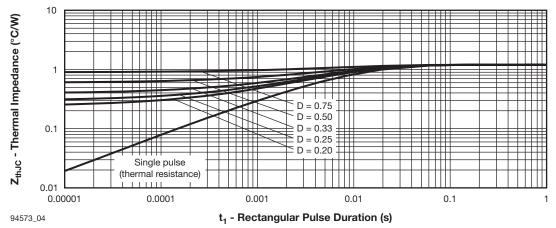


Fig. 4 - Maximum Thermal Impedance  $Z_{thJC}$  Characteristics



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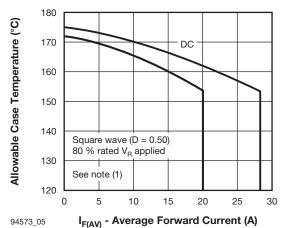


Fig. 5 - Maximum Allowable Case Temperature vs.
Average Forward Current

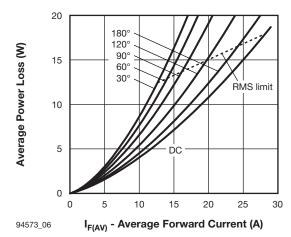


Fig. 6 - Forward Power Loss Characteristics

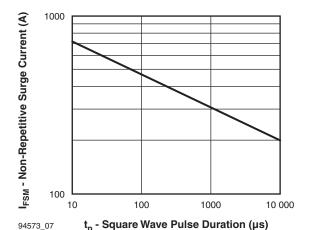


Fig. 7 - Maximum Non-Repetitive Surge Current

#### Note

 $^{(1)}$  Formula used: T<sub>C</sub> = T<sub>J</sub> - (Pd + Pd<sub>REV</sub>) x R<sub>th,JC</sub>; Pd = Forward power loss = I<sub>F(AV)</sub> x V<sub>FM</sub> at (I<sub>F(AV)</sub>/D) (see fig. 6); Pd<sub>REV</sub> = Inverse power loss = V<sub>R1</sub> x I<sub>R</sub> (1 - D); I<sub>R</sub> at V<sub>R1</sub> = 80 % rated V<sub>R</sub>

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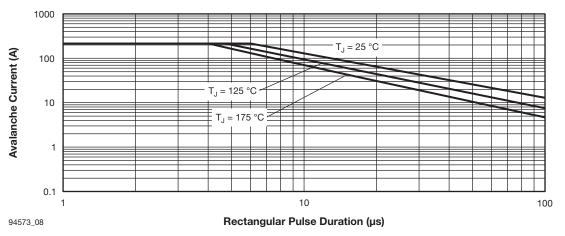


Fig. 8 - Reverse Bias Safe Operating Area (Avalanche Current vs. Rectangular Pulse Duration)

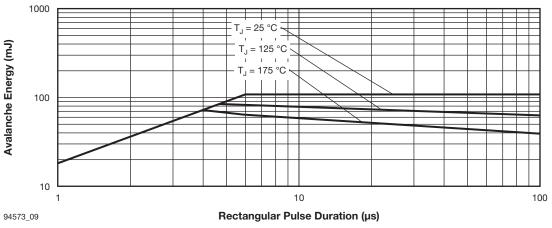


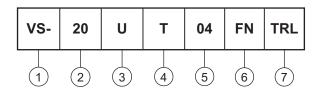
Fig. 9 - Reverse Bias Safe Operating Area (Avalanche Energy vs. Rectangular Pulse Duration)



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#### **ORDERING INFORMATION TABLE**

**Device code** 



1 - Vishay Semiconductors product

Current rating (20 A)

- Package:

• U = I-PAK

• W = D-PAK

4 - T = Trench

5 - Voltage code (45 V)

6 - TO-252AA (D-PAK)

7 - D-PAK, I-PAK:

None = Tube (75 pieces)

D-PAK only:

• TR = Tape and reel

• TRL = Tape and reel (left oriented)

• TRR = Tape and reel (right oriented)

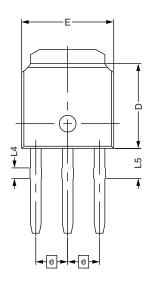
LINKS TO RELATED DOCUMENTS					
Dimensions	I-PAK (TO-251AA)	www.vishay.com/doc?95024			
Differsions	D-PAK (TO-252AA)	www.vishay.com/doc?95448			
Dout an adding information	I-PAK (TO-251AA)	www.vishay.com/doc?95025			
Part marking information	D-PAK (TO-252AA)	www.vishay.com/doc?95059			
Packaging information		www.vishay.com/doc?95033			
SPICE model		www.vishay.com/doc?95027			

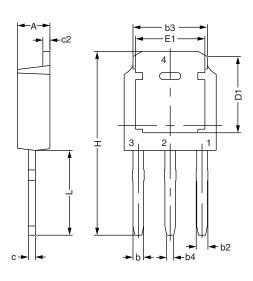


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## I-PAK - S

#### **DIMENSIONS FOR I-PAK - S** in millimeters





SYMBOL	DIMENSIONAL REQUIREMENTS				
STWIBOL	MIN.	NOM.	MAX.		
E	6.40	6.60	6.70		
L	3.98	4.13	4.28		
L4	0.66	0.76	0.86		
L5	1.96	2.16	2.36		
D	6.00	6.10	6.20		
Н	11.05	11.25	11.45		
b	0.64	0.76	0.88		
b2	0.77	0.84	1.14		
b3	5.21	5.34	5.46		
b4	0.41 0.51		0.61		
е	2.286 BSC				
Α	2.20	2.30	2.38		
С	0.40	0.50	0.60		
c2	0.40	0.50	0.60		
D1	5.30	-	-		
E1	4.40	-	-		



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